

HOMOJUNCTION SEMICONDUCTOR DEVICE AND MANUFACTURE OF PHOTOELECTRIC CONVERSION DEVICE USING THE SAME

Patent number: JP6097481

Publication date: 1994-04-08

Inventor: FURUBIKI SHIGEMI; NEGAMI TAKAYUKI; NISHITANI MIKIHIKO; WADA TAKAHIRO

Applicant: MATSUSHITA ELECTRIC IND CO LTD

Classification:

- **International:** H01L31/04

- **European:**

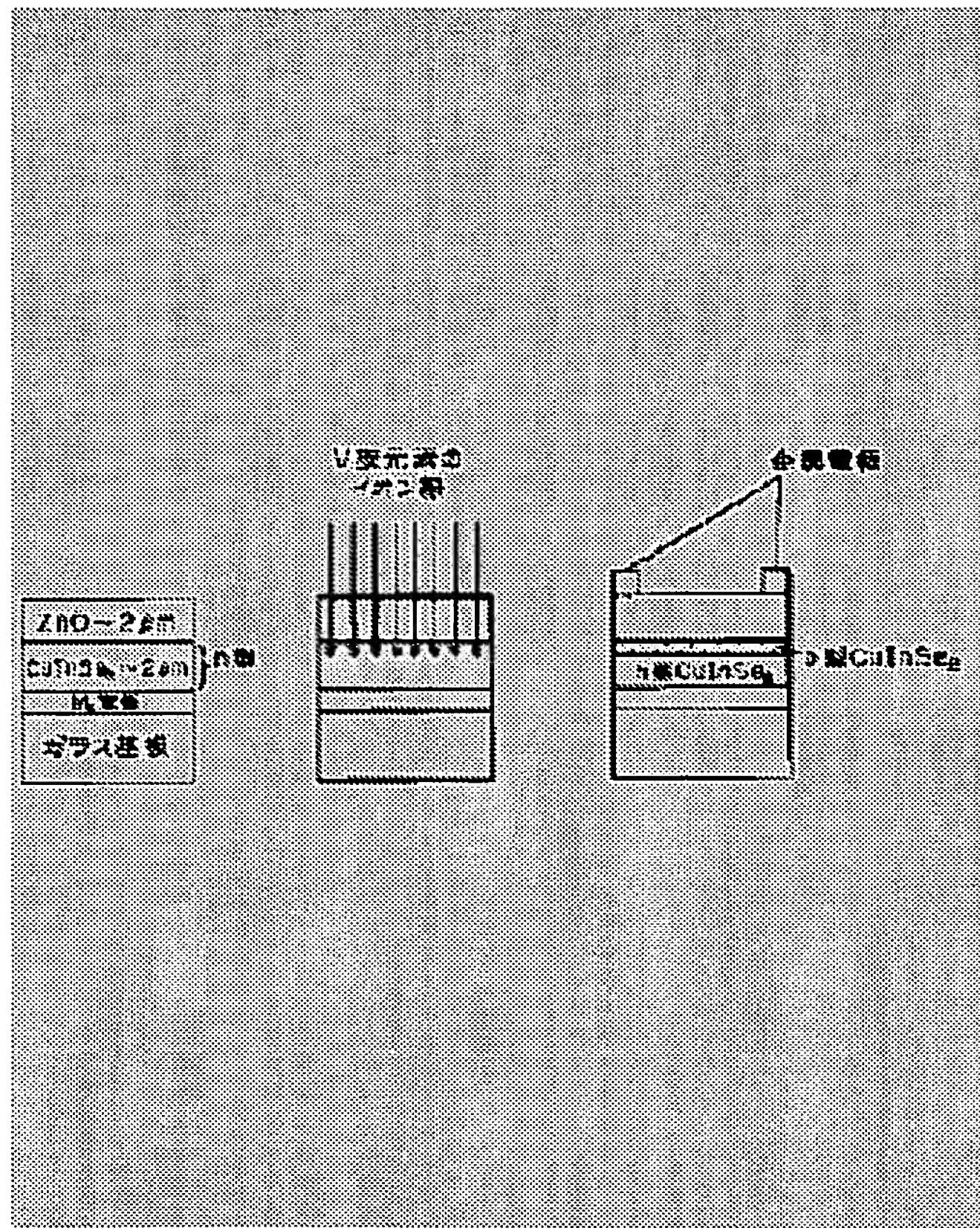
Application number: JP19920244375 19920914

Priority number(s): JP19920244375 19920914

[Report a data error here](#)

Abstract of JP6097481

PURPOSE: To provide a homojunction semiconductor device having an improved device characteristic, which can be matched with the semiconductor thin film made of I-III-(IV)2 chalcopyrite compound in its lattice constant, its orientation quality to substrate surface and its surface morphology and to provide a photoelectric conversion semiconductor device using the same. **CONSTITUTION:** On an Mo lower electrode, an element having CuInSe₂, ZnO and ITO thin films is manufactured. An ionic radiation of nitrogen atom is acceleration-projected thereon, and a homojunction is formed in the CuInSe₂ thin film, and thereby, a photoelectric conversion semiconductor device is created.



Data supplied from the esp@cenet database - Worldwide